



2SA1416/2SC3646

High-Voltage Switching Applications

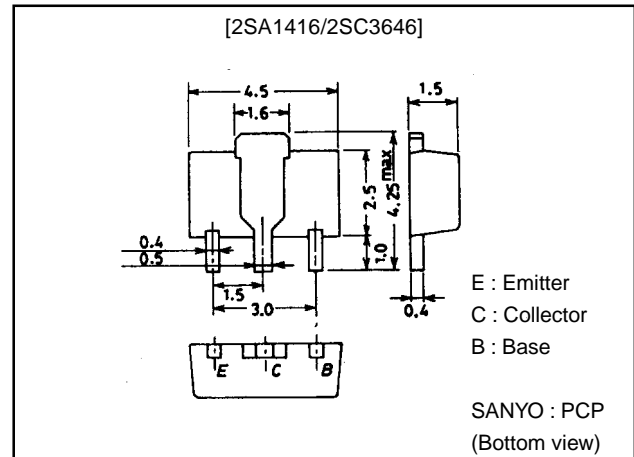
Features

- Adoption of FBET, MBIT processes.
- High breakdown voltage and large current capacity.
- Fast switching time.
- Very small size making it easy to provide high-density, small-sized hybrid ICs.

Package Dimensions

unit:mm

2038



() : 2SA1416

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		(-120)	V
Collector-to-Emitter Voltage	V_{CEO}		(-100)	V
Emitter-to-Base Voltage	V_{EBO}		(-6)	V
Collector Current	I_C		(-1)	A
Collector Current (Pulse)	I_{CP}		(-2)	A
Collector Dissipation	P_C		500	mW
		Mounted on ceramic board (250mm ² ×0.8mm)	1.3	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)100\text{V}, I_E = 0$			(-100)	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4\text{V}, I_C = 0$			(-100)	nA
DC Current Gain	h_{FE}	$V_{CE} = (-)5\text{V}, I_C = (-)100\text{mA}$	100*		400*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10\text{V}, I_C = (-)100\text{mA}$		120		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-)10\text{V}, f = 1\text{MHz}$		(13)		pF
				8.5		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)400\text{mA}, I_B = (-)40\text{mA}$		(-0.2)	(-0.6)	V
				0.1	0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)400\text{mA}, I_B = (-)40\text{mA}$		(-0.85)	(-1.2)	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu\text{A}, I_E = 0$	(-120)			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{mA}, R_{BE} = \infty$	(-100)			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu\text{A}, I_C = 0$	(-6)			V
Turn-ON Time	t_{on}	See specified Test Circuit.		(80)		ns
				80		ns
Storage Time	t_{stg}	See specified Test Circuit.		(700)		ns
				850		ns
Fall Time	t_f	See specified Test Circuit.		(40)		ns
				50		ns

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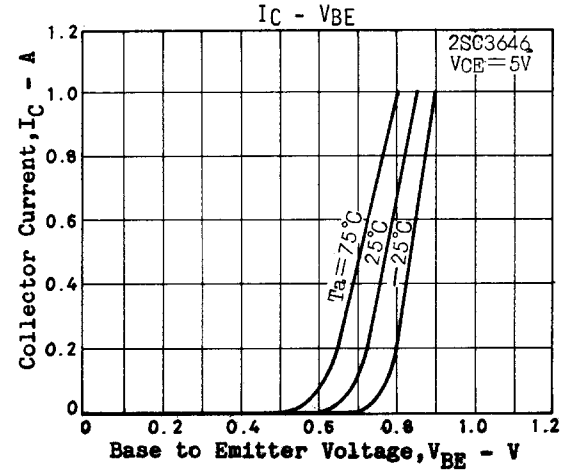
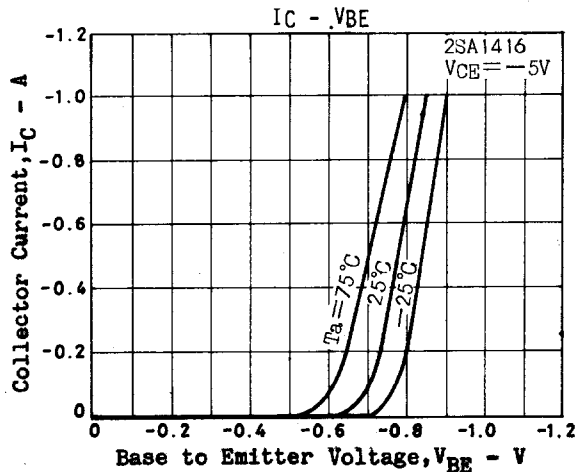
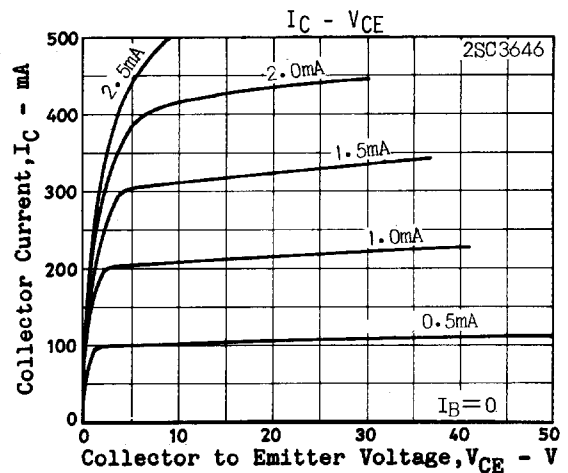
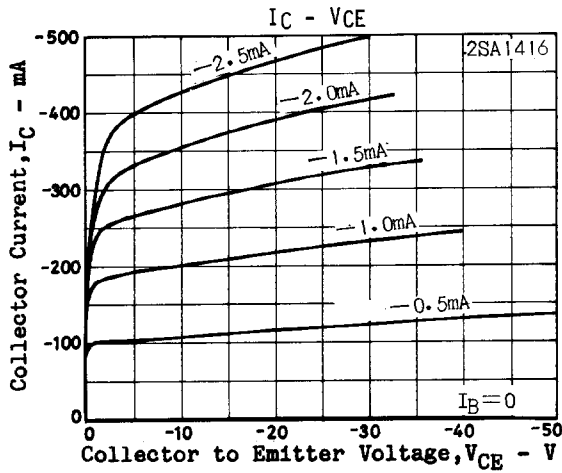
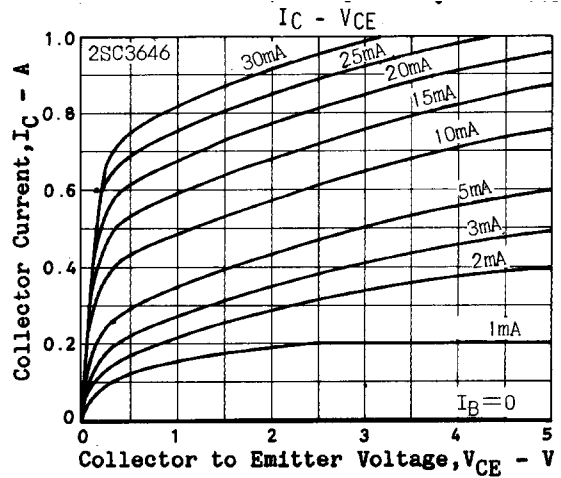
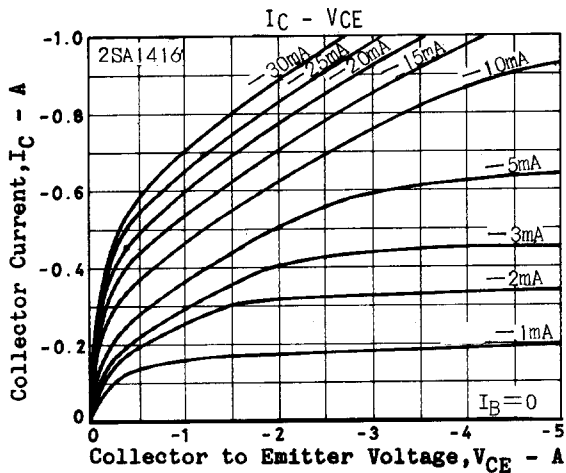
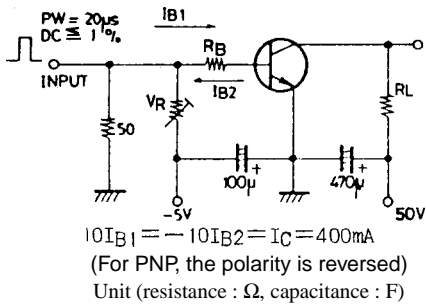
2SA1416/2SC3646

* : The 2SA1416/2SC3646 are classified by 100mA h_{FE} as follows :

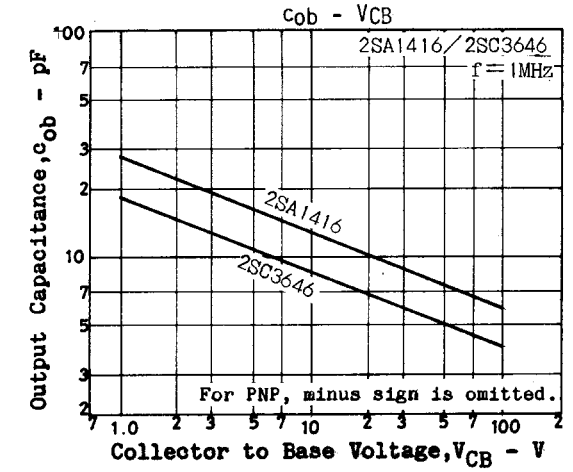
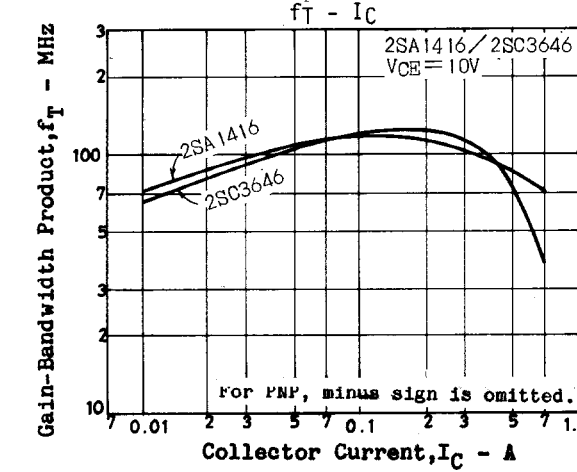
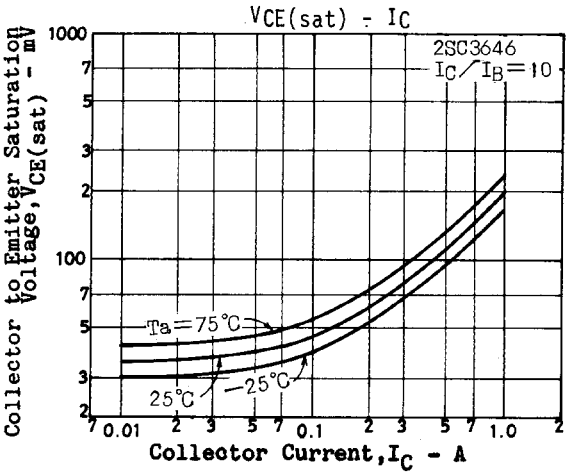
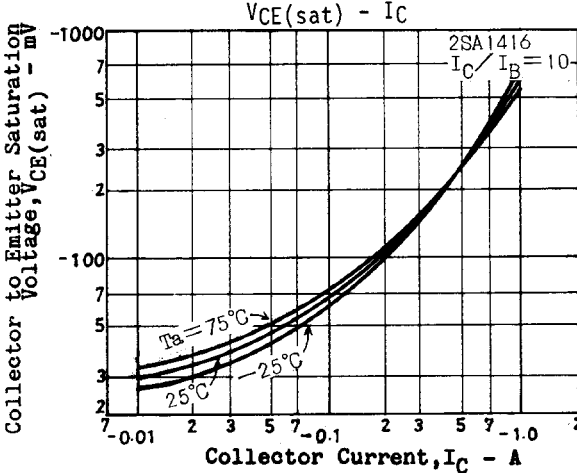
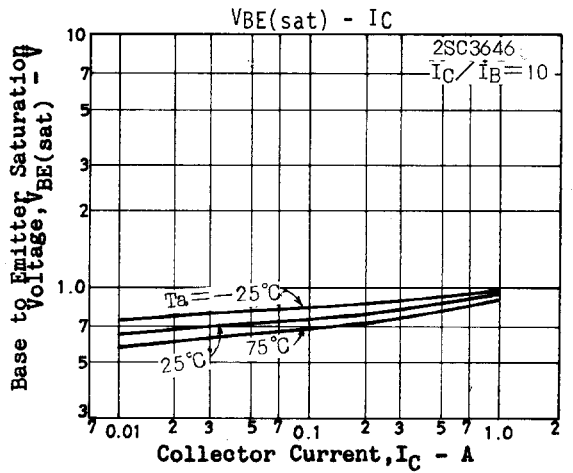
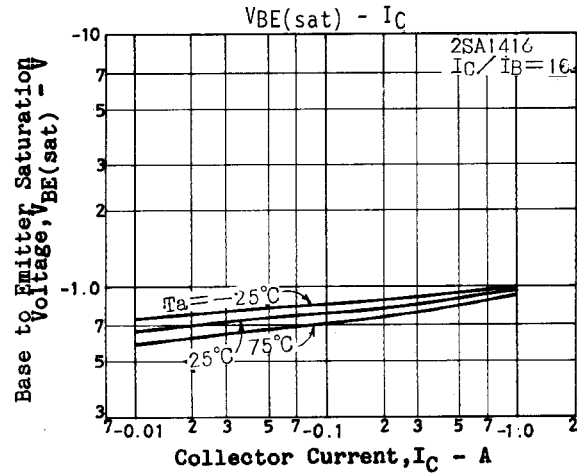
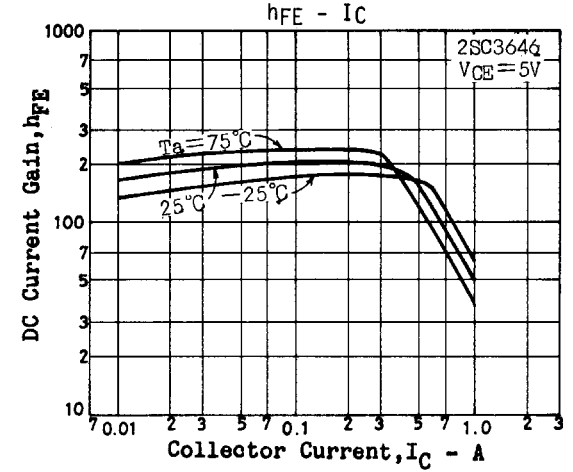
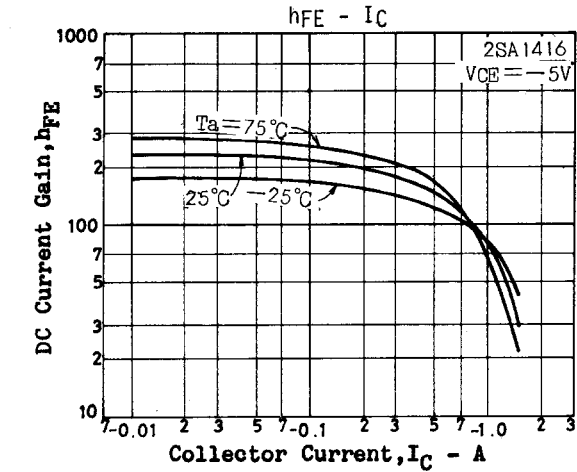
100	R	200	140	S	280	200	T	400
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Marking 2SA1416 : AB h_{FE} rank : R, S, T
 2SC3646 : CB

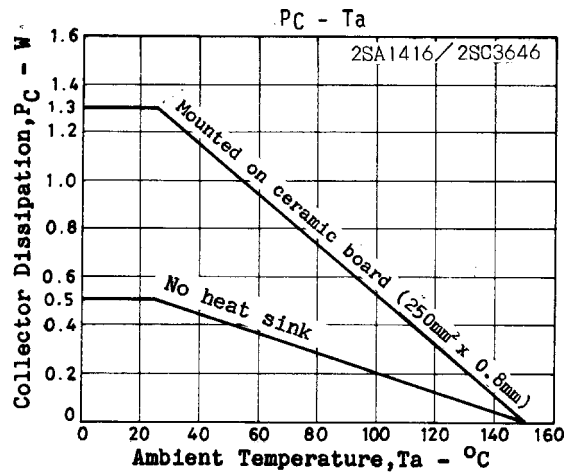
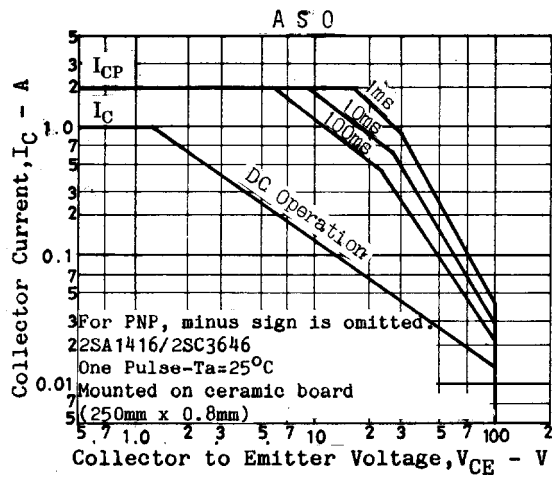
Switching Time Test Circuit



2SA1416/2SC3646



2SA1416/2SC3646



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